	U	1	Document ID	Title
1			US 20040065903 A1	Integrated circuit with MOSFETS having bi-layer metal gate electordes and method of making same
2	X		US 6879009 B2	Integrated circuit with MOSFETS having bi-layer metal gate electrodes
3	X		US 6696333 B1	Method of making integrated circuit with MOSFETs having bi-layer metal gate electrodes
4	X		US 6479403 B1	Method to pattern polysilicon gates with high-k material gate dielectric
5	X		US 6380063 B1	Raised wall isolation device with spacer isolated contacts and the method of so forming
6	X		US 6218276 B1	Silicide encapsulation of polysilicon gate and interconnect

	U	1	Document ID	Title
7	X		US 6100173 A	Forming a self-aligned silicide gate conductor to a greater thickness than junction silicide structures using a dual-salicidation process
8	X		US 6638829 B	Manufacture of semiconductor structure by forming polysilicon alignment structure, growing epitaxial layer, removing polysilicon alignment structure, planarizing and etching oxide layer, forming silicide layer, and forming gate electrode
9	X		US 6218276 B	Formation of semiconductor device by forming refractory metal silicide layer on vertical sidewall surfaces of gate electrode, on top surface of gate electrode, and on source and drain regions

	Type	L #	Hits	Search Text	DBs
1	BRS	L1	483	(((spacer$1) near35 (gate)) near25 (remov$3)) near25 (silicide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
2	BRS	L2	335	(((sidewall$1) near35 (gate)) near25 (remov$3)) near25 (silicide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
3	BRS	L3	126	(((side near wall$1) near35 (gate)) near25 (remov$3)) near25 (silicide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
4	BRS	L4	1161	(((spacer$1) near35 (gate)) near25 (remov$3)) near25 (silicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Type	L #	Hits	Search Text	DBs
5	BRS	L5	709	4 and silicide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
6	BRS	L6	138	(((spacer$1) near35 (gate)) near25 (remov$3)) near25 (silicon) near15 (silicide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
7	BRS	L7	190	((silicide near15 silicon) near25 (spacer$1)) near25 (remov$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
8	BRS	L8	159	((silicide near15 silicon) near25 (sidewall$1)) near25 (remov$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Type	L #	Hits	Search Text	DBs
9	BRS	L9	56	((silicide near15 silicon) near25 (side near wall$1)) near25 (remov$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
10	BRS	L10	1862	(remov$3) near15 (gate near dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
11	BRS	L11	311	((remov$3) near15 (gate near dielectric)) near25 (spacer$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
12	BRS	L12	287	((remov$3) near15 (gate near dielectric)) near25 (sidewall$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Type	L #	Hits	Search Text	DBs
13	BRS	L13	28	((remov$3) near15 (gate near dielectric)) near25 (side near wall$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB